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D
1 45. (Twice Amended) The capacitors of claim 44 wherein each
2 comprises:

3 a stem; and

4 in cross-section, at least two laterally opposed fins interconnected
5 with and projecting laterally from the stem, the stem having a minimum
6 width which is less than the minimum photolithographic feature
7 dimension [with which the capacitors are fabricated].

8
9 New Claims

10
11 51
46. The capacitors of claim 44, wherein the lower plates are
12 formed from conductive polysilicon.

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14 52
47. The capacitors of claim 45, wherein the stem and fins are
15 formed from conductive polysilicon.

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17 53
48. The capacitors of claim 45, wherein the pair of stacked
18 capacitors are coated with a capacitor dielectric layer.
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49. A pair of adjacent stacked capacitors fabricated relative to
2 a semiconductor substrate, the adjacent stacked capacitors respectively
3 including a lower plate having a minimum lateral spacing from one
4 another which is less than a minimum photolithographic feature
5 dimension, each lower plate comprising a stem and, in cross-section, at
6 least two laterally opposed fins interconnected with and projecting
7 laterally from the stem.

8 ⁵⁵
9 50. The capacitors of claim ⁵⁴~~49~~, wherein the minimum
10 photolithographic feature dimension is one with which the capacitors are
11 fabricated.

12 ⁵⁶
13 51. The capacitors of claim ⁵⁴~~49~~ wherein the stem includes a
14 minimum width which is less than the minimum photolithographic feature
15 dimension.

16 ⁵⁷
17 52. The capacitors of claim ⁵⁶~~51~~, wherein the minimum
18 photolithographic feature dimension is one with which the capacitors are
19 fabricated.

20 ⁵⁸
21 53. The capacitors of claim ⁵⁶~~49~~, wherein the lower plates are
22 formed from conductive polysilicon.
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1 59
2 54. The capacitors of claim ~~49~~⁵⁶, wherein the stem and fins are
3 formed from conductive polysilicon.

4 60
5 55. The capacitors of claim ~~49~~⁵⁶, wherein the pair of stacked
6 capacitors are coated with a capacitor dielectric layer.

7 61
8 56. A pair of adjacent stacked capacitors fabricated relative to
9 a semiconductor substrate, the adjacent stacked capacitors respectively
10 including a finned lower plate having a minimum lateral spacing from
11 one another which is less than a minimum photolithographic feature
12 dimension.

13 62
14 57. The capacitors of claim ~~56~~⁶¹ wherein each comprises:
15 a stem; and
16 in cross-section, at least two laterally opposed fins interconnected
17 with and projecting laterally from the stem, the stem having a minimum
18 width which is less than the minimum photolithographic feature
19 dimension.

20 63
21 58. The capacitors of claim ~~56~~⁶¹, wherein the minimum
22 photolithographic feature dimension is one with which the capacitors are
23 fabricated.

64
59. The capacitors of claim 51 wherein the stem includes a minimum width which is less than the minimum photolithographic feature dimension.

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D cont
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60. The capacitors of claim 59, wherein the minimum photolithographic feature dimension is one with which the capacitors are fabricated.

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61. The capacitors of claim 56, wherein the lower plates are formed from conductive polysilicon.

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62. The capacitors of claim 57, wherein the stem and fins are formed from conductive polysilicon.

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63. The capacitors of claim 56, wherein the pair of stacked capacitors are coated with a capacitor dielectric layer.